



# P-Channel Enhancement-Mode Vertical DMOS FET

## Features

- ▶ High input impedance and high gain
- ▶ Low power drive requirement
- ▶ Ease of paralleling
- ▶ Low  $C_{ISS}$  and fast switching speeds
- ▶ Excellent thermal stability
- ▶ Integral source-drain diode
- ▶ Free from secondary breakdown

## Applications

- ▶ Logic level interfaces - ideal for TTL and CMOS
- ▶ Solid state relays
- ▶ Analog switches
- ▶ Power management
- ▶ Telecom switches

## General Description

This low threshold, enhancement-mode (normally-off) transistor utilizes a vertical DMOS structure and Supertex's well-proven, silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

## Ordering Information

Part Number	Package Option	Packing
TP2104K1-G	TO-236AB (SOT-23)	3000/Reel
TP2104N3-G	3-Lead TO-92	1000/Bag
TP2104N3-G P002	3-Lead TO-92	2000/Reel
TP2104N3-G P003		
TP2104N3-G P005		
TP2104N3-G P013		
TP2104N3-G P014		

-G denotes a lead (Pb)-free / RoHS compliant package.  
 Contact factory for Wafer / Die availability.  
 Devices in Wafer / Die form are lead (Pb)-free / RoHS compliant.

## Absolute Maximum Ratings

Parameter	Value
Drain-to-source voltage	$BV_{DSS}$
Drain-to-gate voltage	$BV_{DGS}$
Gate-to-source voltage	$\pm 20V$
Operating and storage temperature	$-55^{\circ}C$ to $+150^{\circ}C$

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

## Typical Thermal Resistance

Package	$\theta_{ja}$
TO-236AB (SOT-23)	$203^{\circ}C/W$
TO-92	$132^{\circ}C/W$

## Product Summary

$BV_{DSS}/BV_{DGS}$	$R_{DS(ON)}$ (max)	$V_{GS(th)}$ (max)
-40V	$6.0\Omega$	-2.0V

## Pin Configuration



## Product Marking

**P1LW** W = Code for week sealed  
 \_\_\_\_\_ = "Green" Packaging

Package may or may not include the following marks: Si or   
**TO-236AB (SOT-23)**

**SiTP** YY = Year Sealed  
**2 1 0 4** WW = Week Sealed  
**YYWW** \_\_\_\_\_ = "Green" Packaging

Package may or may not include the following marks: Si or   
**TO-92**

## Thermal Characteristics

Package	$I_D$ (continuous) <sup>†</sup>	$I_D$ (pulsed)	Power Dissipation @ $T_A = 25^\circ\text{C}$	$I_{DR}$ <sup>†</sup>	$I_{DRM}$
TO-236AB (SOT-23)	-160mA	-800mA	0.36W	-160mA	-800mA
TO-92	-175mA	-1.0A	0.74W	-175mA	-1.0A

<sup>†</sup>  $I_D$  (continuous) is limited by max rated  $T_J$ .

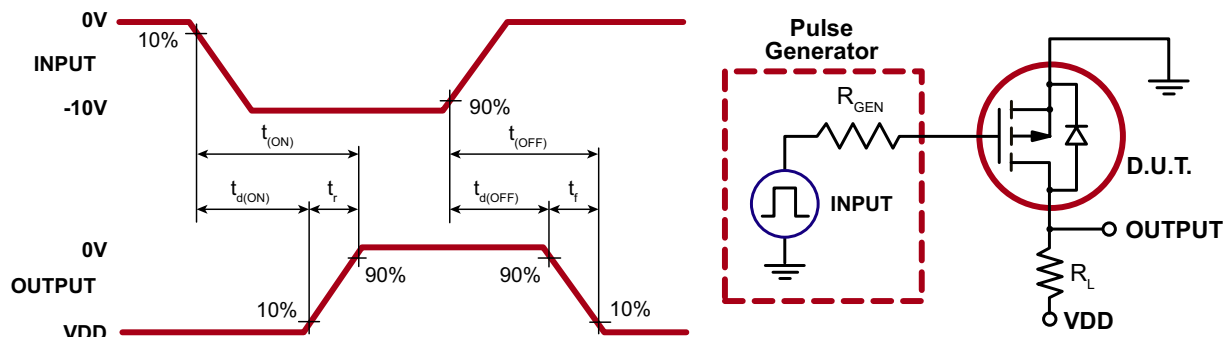
## Electrical Characteristics ( $T_A = 25^\circ\text{C}$ unless otherwise specified)

Sym	Parameter	Min	Typ	Max	Units	Conditions
$BV_{DSS}$	Drain-to-source breakdown voltage	-40	-	-	V	$V_{GS} = 0V, I_D = -1.0mA$
$V_{GS(th)}$	Gate threshold voltage	-1.0	-	-2.0	V	$V_{GS} = V_{DS}, I_D = -1.0mA$
$\Delta V_{GS(th)}$	Change in $V_{GS(th)}$ with temperature	-	5.8	6.5	mV/°C	$V_{GS} = V_{DS}, I_D = -1.0mA$
$I_{GSS}$	Gate body leakage	-	-1.0	-100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
$I_{DSS}$	Zero gate voltage drain current	-	-	-10	$\mu\text{A}$	$V_{GS} = 0V, V_{DS} = \text{Max Rating}$
		-	-	-1.0	mA	$V_{DS} = 0.8 \text{ Max Rating}, V_{GS} = 0V, T_A = 125^\circ\text{C}$
$I_{D(ON)}$	On-state drain current	-0.6	-	-	A	$V_{GS} = -10V, V_{DS} = -25V$
$R_{DS(ON)}$	Static drain-to-source on-state resistance	-	-	10	$\Omega$	$V_{GS} = -4.5V, I_D = -50mA$
		-	-	6.0		$V_{GS} = -10V, I_D = -500mA$
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with temperature	-	0.55	1.0	%/°C	$V_{GS} = -10V, I_D = -500mA$
$G_{FS}$	Forward transconductance	150	200	-	mmho	$V_{DS} = -25V, I_D = -500mA$
$C_{ISS}$	Input capacitance	-	35	60	pF	$V_{GS} = 0V, V_{DS} = -25V, f = 1.0 \text{ MHz}$
$C_{OSS}$	Common source output capacitance	-	22	30		
$C_{RSS}$	Reverse transfer capacitance	-	8.0	10		
$t_{d(ON)}$	Turn-on delay time	-	4.0	6.0	ns	$V_{DD} = -25V, I_D = -500mA, R_{GEN} = 25\Omega$
$t_r$	Rise time	-	4.0	8.0		
$t_{d(OFF)}$	Turn-off delay time	-	5.0	9.0		
$t_f$	Fall time	-	5.0	8.0		
$V_{SD}$	Diode forward voltage drop	-	-1.2	-2.0	V	$V_{GS} = 0V, I_{SD} = -500mA$
$t_{rr}$	Reverse recovery time	-	400	-	ns	$V_{GS} = 0V, I_{SD} = -500mA$

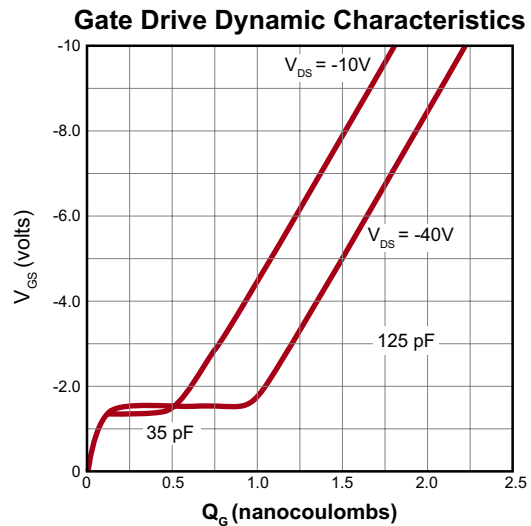
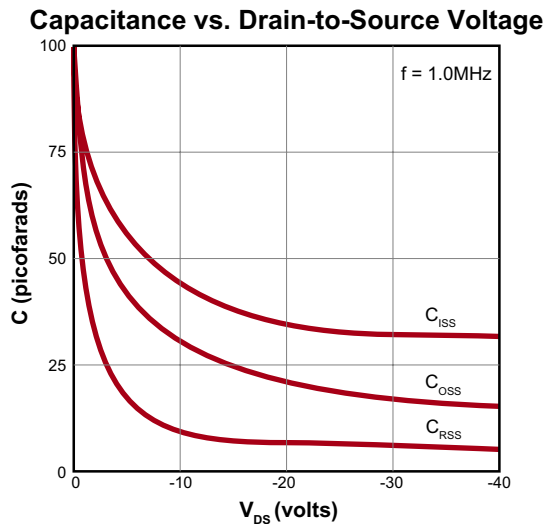
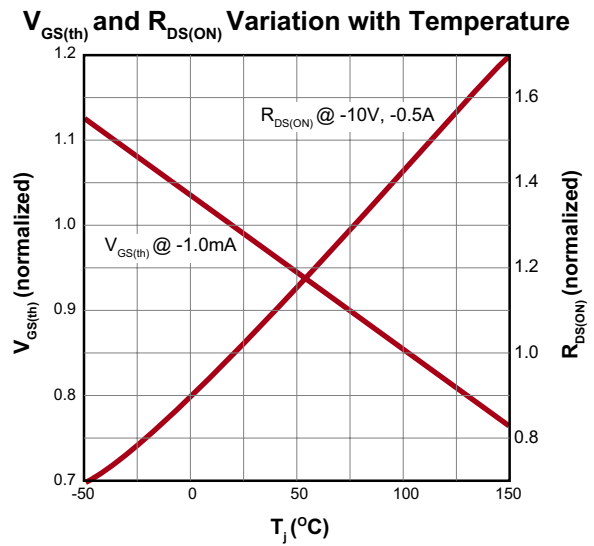
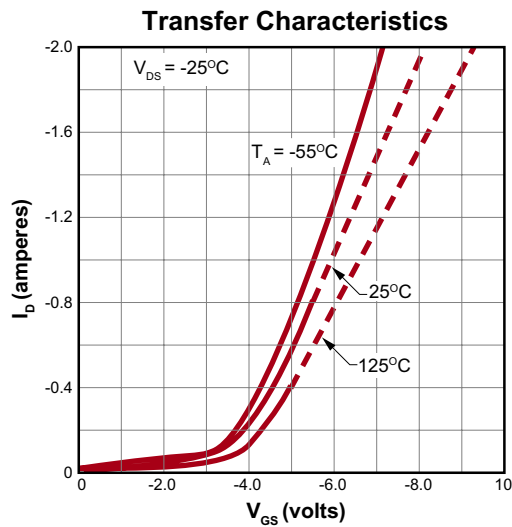
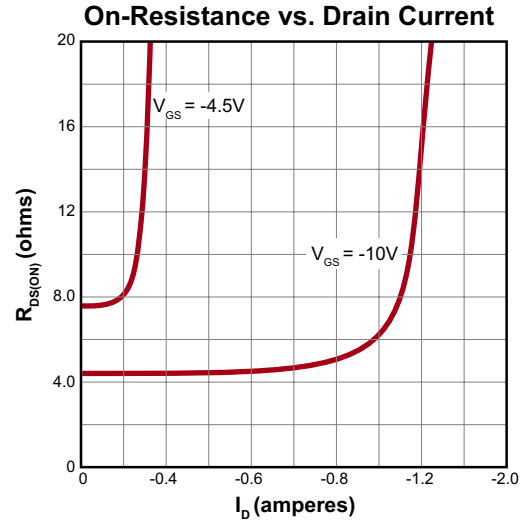
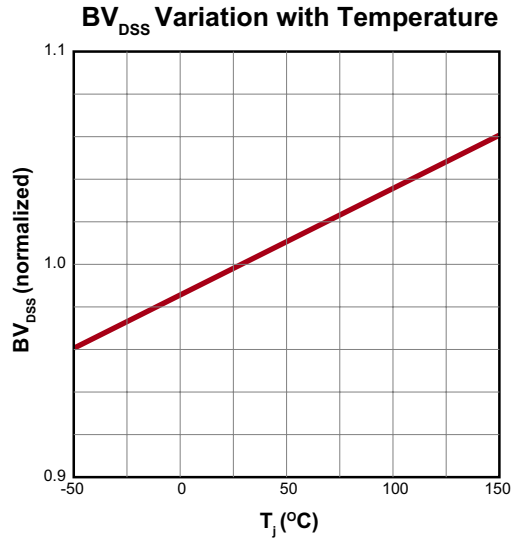
### Notes:

- All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)
- All A.C. parameters sample tested.

## Switching Waveforms and Test Circuit

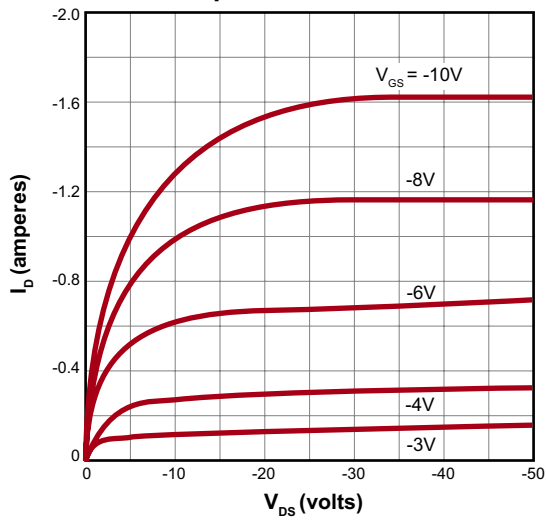


# Typical Performance Curves

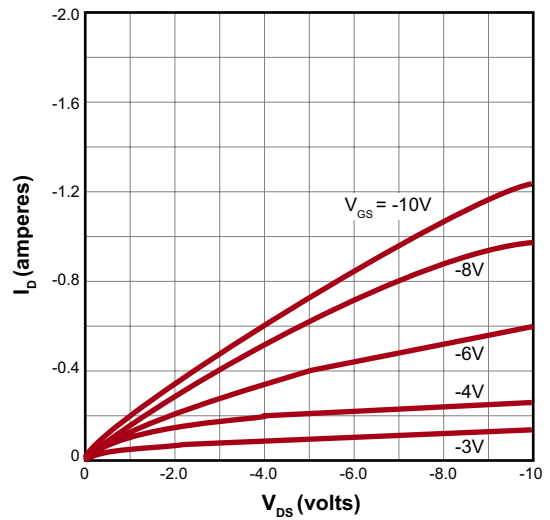


Typical Performance Curves (cont.)

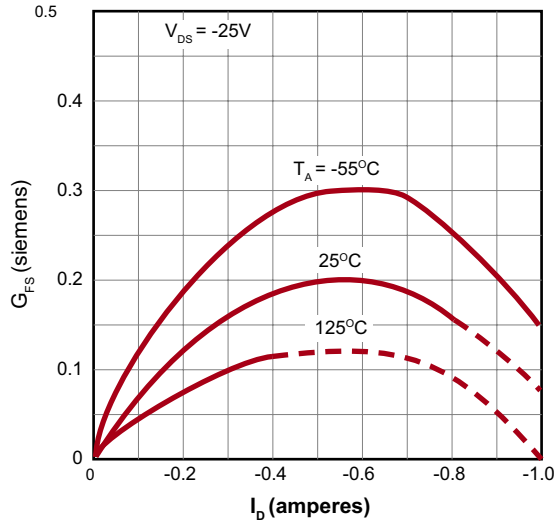
Output Characteristics



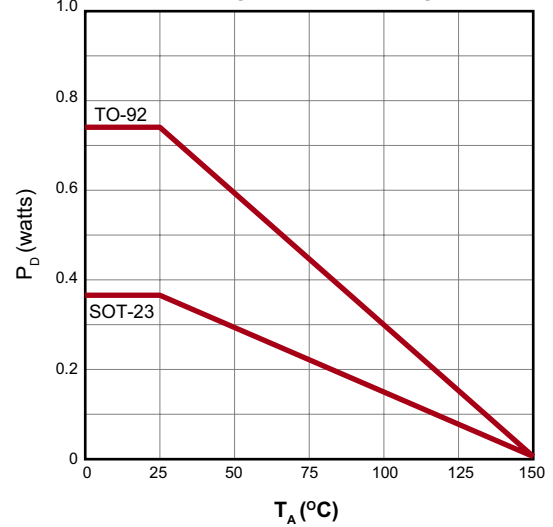
Saturation Characteristics



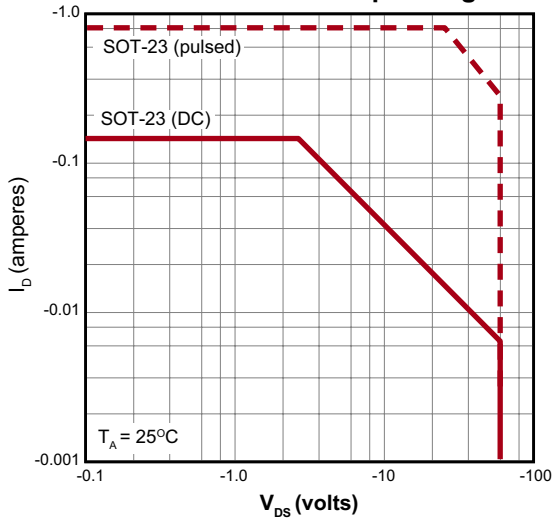
Transconductance vs. Drain Current



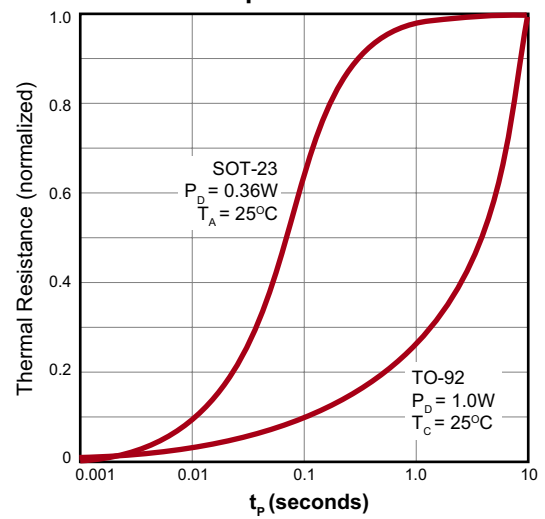
Power Dissipation vs. Temperature



Maximum Rated Safe Operating Area

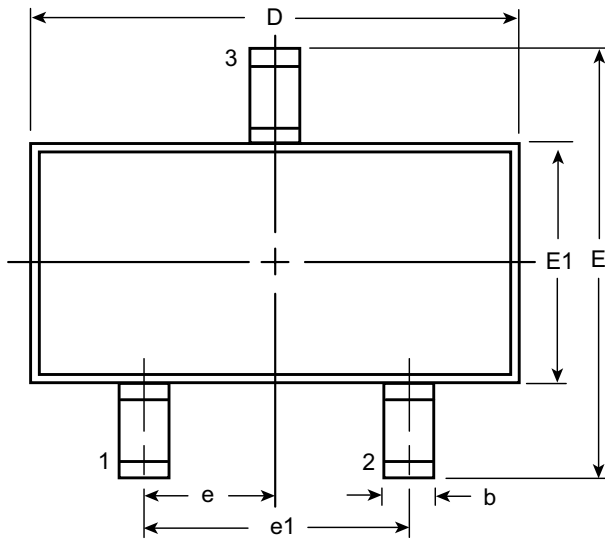


Thermal Response Characteristics

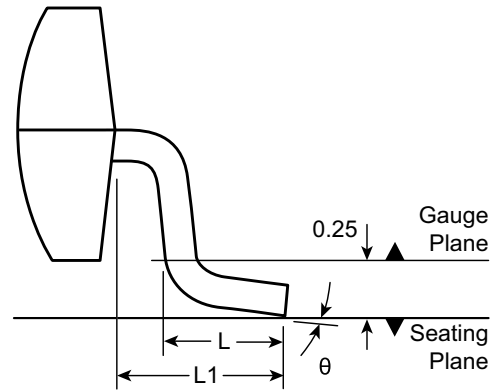


### 3-Lead TO-236AB (SOT-23) Package Outline (K1)

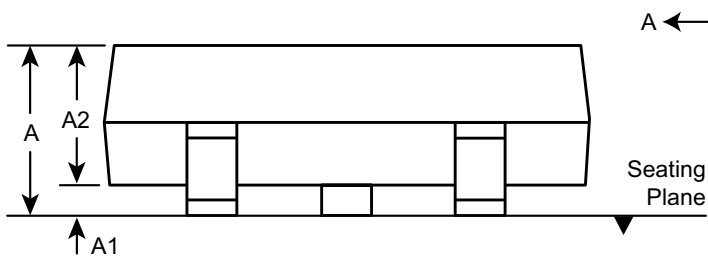
2.90x1.30mm body, 1.12mm height (max), 1.90mm pitch



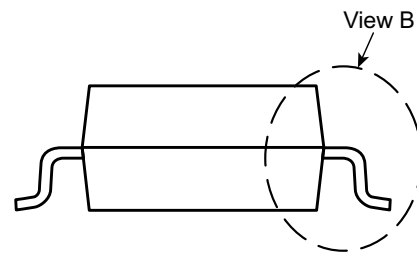
**Top View**



**View B**



**Side View**



**View A - A**

Symbol	A	A1	A2	b	D	E	E1	e	e1	L	L1	$\theta$	
Dimension (mm)	MIN	0.89	0.01	0.88	0.30	2.80	2.10	1.20	0.95 BSC	1.90 BSC	0.20 <sup>†</sup> 0.50 0.60	0.54 REF	0°
	NOM	-	-	0.95	-	2.90	-	1.30					-
	MAX	1.12	0.10	1.02	0.50	3.04	2.64	1.40					8°

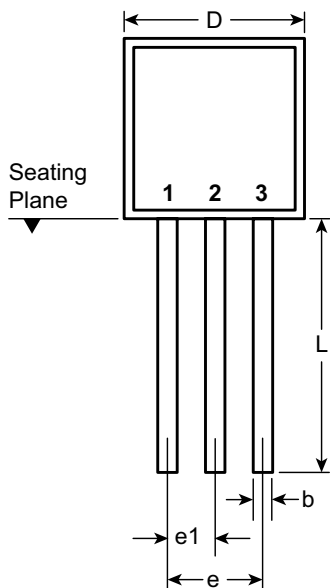
JEDEC Registration TO-236, Variation AB, Issue H, Jan. 1999.

<sup>†</sup> This dimension differs from the JEDEC drawing.

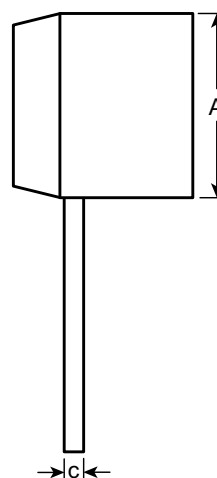
Drawings not to scale.

Supertex Doc.#: DSPD-3TO236ABK1, Version C041309.

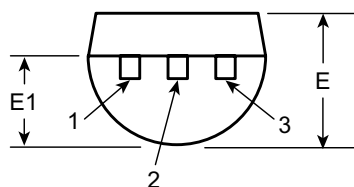
### 3-Lead TO-92 Package Outline (N3)



**Front View**



**Side View**



**Bottom View**

Symbol	A	b	c	D	E	E1	e	e1	L	
Dimensions (inches)	MIN	.170	.014 <sup>†</sup>	.014 <sup>†</sup>	.175	.125	.080	.095	.045	.500
	NOM	-	-	-	-	-	-	-	-	-
	MAX	.210	.022 <sup>†</sup>	.022 <sup>†</sup>	.205	.165	.105	.105	.055	.610*

JEDEC Registration TO-92.

\* This dimension is not specified in the JEDEC drawing.

† This dimension differs from the JEDEC drawing.

**Drawings not to scale.**

**Supertex Doc.#:** DSPD-3TO92N3, Version E041009.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to <http://www.supertex.com/packaging.html>.)

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[TP2104N3-G P013](#) [TP2104N3-G-P003](#)